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INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)		Docket No.: 901.0120.U1(US) Applicant(s): Fletcher et al.. Filing Date: herewith		Serial No.: To be assigned Group: N/A	
U.S. PATENT DOCUMENTS					
Examiner Initials	Document Number (Number-Kind Code)	Publication Date (MM-DD-YYYY)	Name of Patentee or Applicant	Class	Sub-class
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Examiner's Signature: <i>Long Phany</i>			Date Considered: <i>7/14/05</i>		
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).					